

N-channel 100 V, 3.9 mΩ typ., 180 A, STripFET™ F3 Power MOSFET in H²PAK-2 package

Datasheet - production data

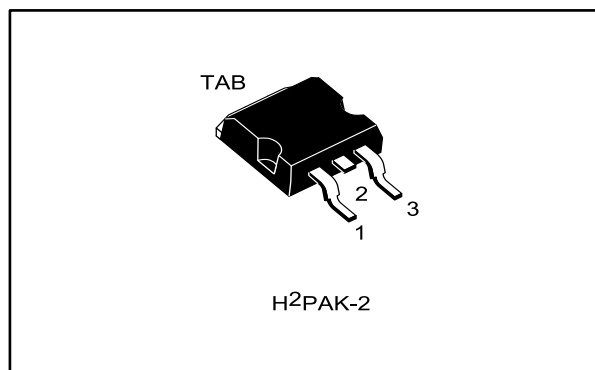
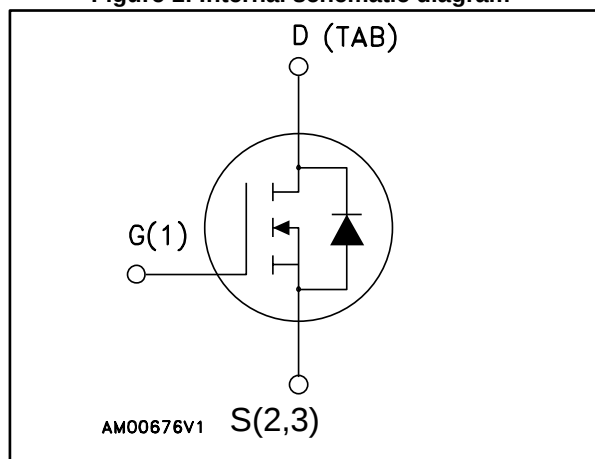


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STH180N10F3-2	100 V	4.5 mΩ	180 A

- Ultra low on-resistance
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using STripFET™ F3 technology. It is designed to minimize on-resistance and gate charge to provide superior switching performance.

Table 1: Device summary

Order code	Marking	Package	Packing
STH180N10F3-2	180N10F3	H ² PAK-2	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	180	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	315	W
	Derating factor	2.1	W/ $^{\circ}\text{C}$
dv/dt	Peak diode recovery voltage slope	20	V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	350	mJ
T_J	Operating junction temperature	-55 to 175	$^{\circ}\text{C}$
T_{stg}	Storage temperature		$^{\circ}\text{C}$

Notes:

⁽¹⁾Current limited by package

⁽²⁾Pulse width limited by safe operating area

⁽³⁾Starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = 80$, $V_{DD} = 50\text{ V}$

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.48	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	35	$^{\circ}\text{C/W}$

Notes:

⁽¹⁾When mounted on FR-4 board of 1 inch², 2 oz Cu

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 4: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage (V _{GS} = 0)	I _D = 250 µA	100			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = 100 V			10	µA
		V _{DS} = 100 V; T _C = 125 °C			100	µA
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±20 V			±200	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 µA	2		4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 60 A		3.9	4.5	mΩ

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0	-	6665	-	pF
C _{oss}	Output capacitance			786		pF
C _{rss}	Reverse transfer capacitance			49		pF
Q _g	Total gate charge	V _{DD} = 50 V, I _D = 120 A		114.6		nC
Q _{gs}	Gate-source charge	V _{GS} = 10 V		38.8		nC
Q _{gd}	Gate-drain charge	See Figure 14: "Gate charge test circuit"		31.9		nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 50 V, I _D = 60 A, R _G = 4.7 Ω, V _{GS} = 10 V See Figure 13: "Switching times test circuit for resistive load"	-	25.6	-	ns
t _r	Rise time			97.1		ns
t _{d(off)}	Turn-off delay time			99.9		ns
t _f	Fall time			6.9		ns

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
I _{SD}	Source-drain current		-		180	A	
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				720	A	
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 120 A, V _{GS} = 0			1.5	V	
t _{rr}	Reverse recovery time	I _{SD} = 120 A, di/dt = 100 A/μs, V _{DD} = 80 V, T _J = 150 °C			83.4		ns
Q _{rr}	Reverse recovery charge				295.7		nC
I _{RRM}	Reverse recovery current				7.1		A

Notes:

⁽¹⁾Pulse width limited by safe operating area

⁽²⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

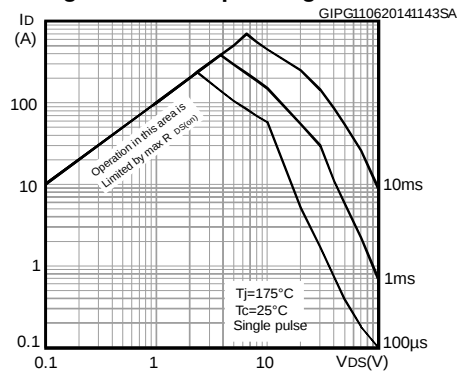


Figure 3: Thermal impedance

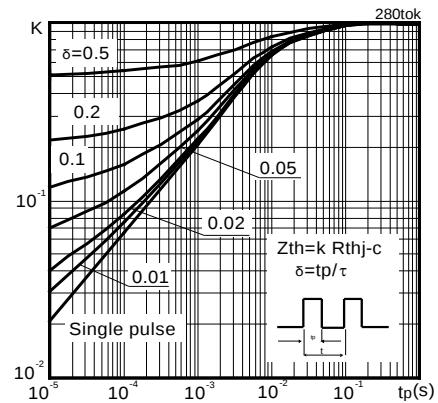


Figure 4: Output characteristics

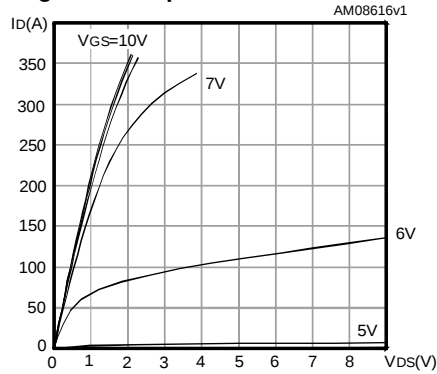


Figure 5: Transfer characteristics

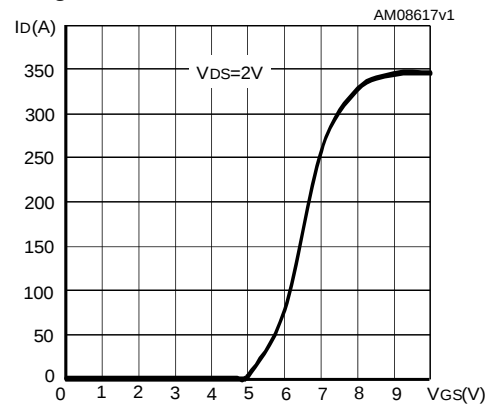
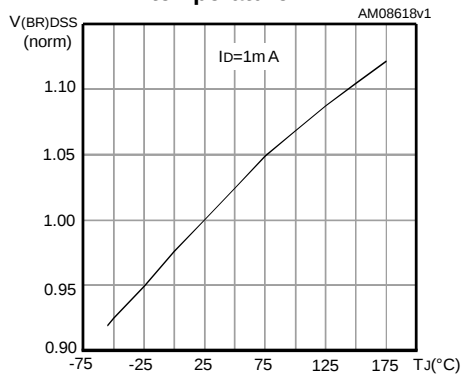
Figure 6: Normalized $V_{(BR)DSS}$ vs temperature

Figure 7: Static drain-source on-resistance

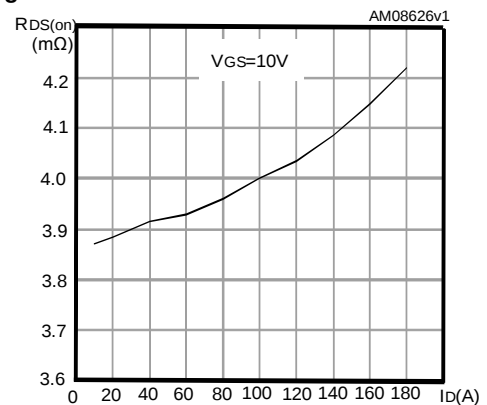


Figure 8: Gate charge vs gate-source voltage

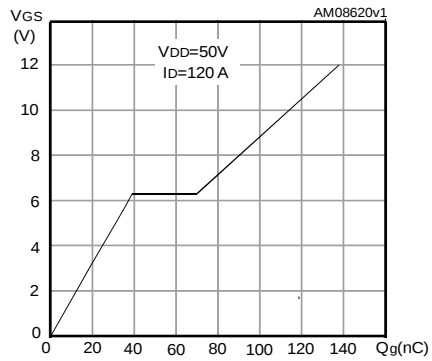


Figure 9: Capacitance variations

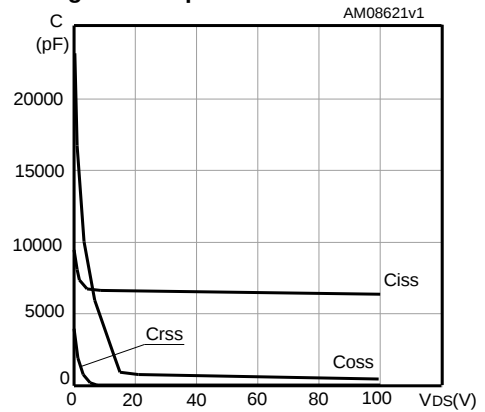


Figure 10: Normalized gate threshold voltage vs temperature

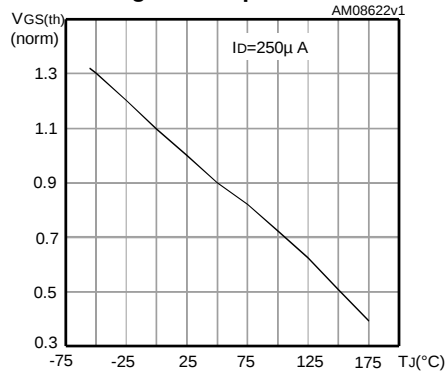


Figure 11: Normalized on-resistance vs temperature

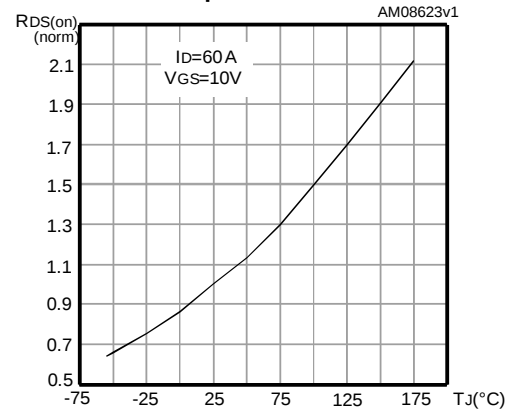
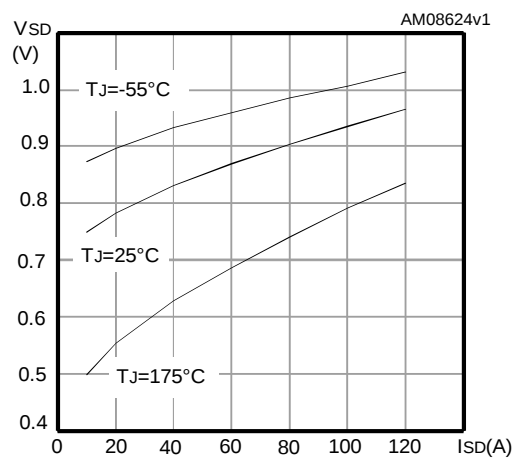


Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Switching times test circuit for resistive load

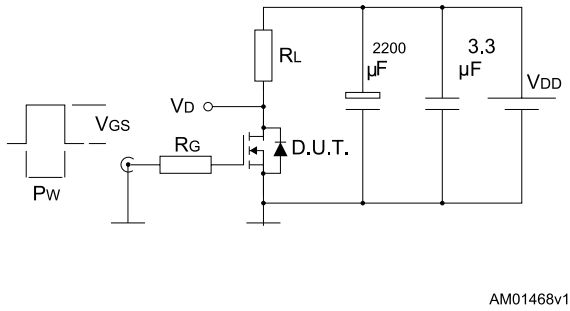


Figure 14: Gate charge test circuit

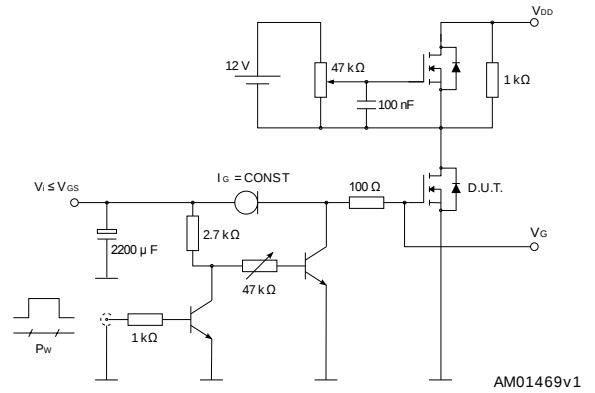


Figure 15: Test circuit for inductive load switching and diode recovery times

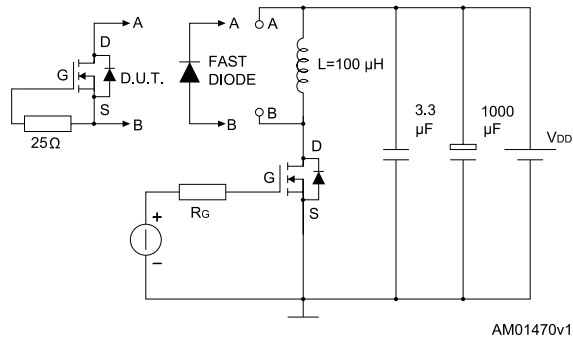


Figure 16: Unclamped inductive load test circuit

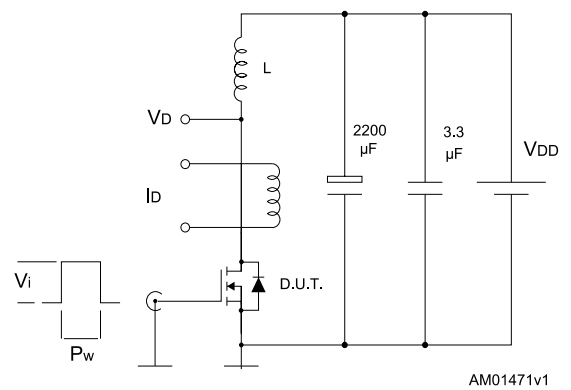


Figure 17: Unclamped inductive waveform

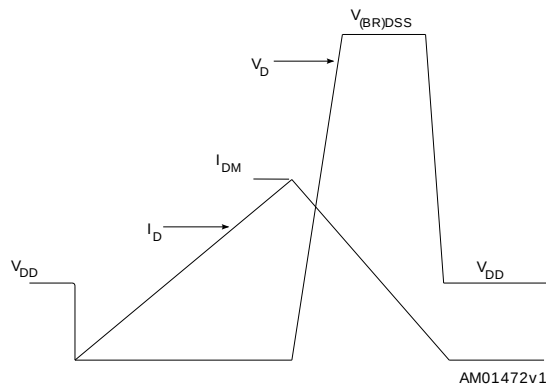
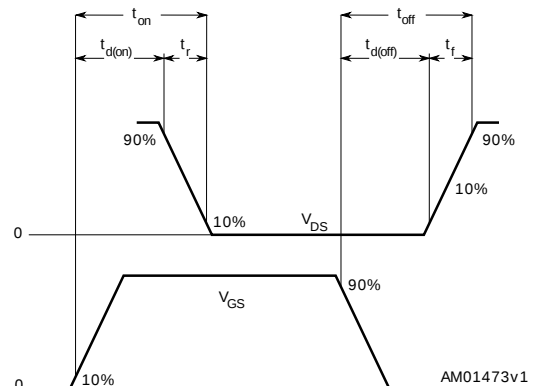


Figure 18: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK[®] is an ST trademark.

4.1 H²PAK-2 package information

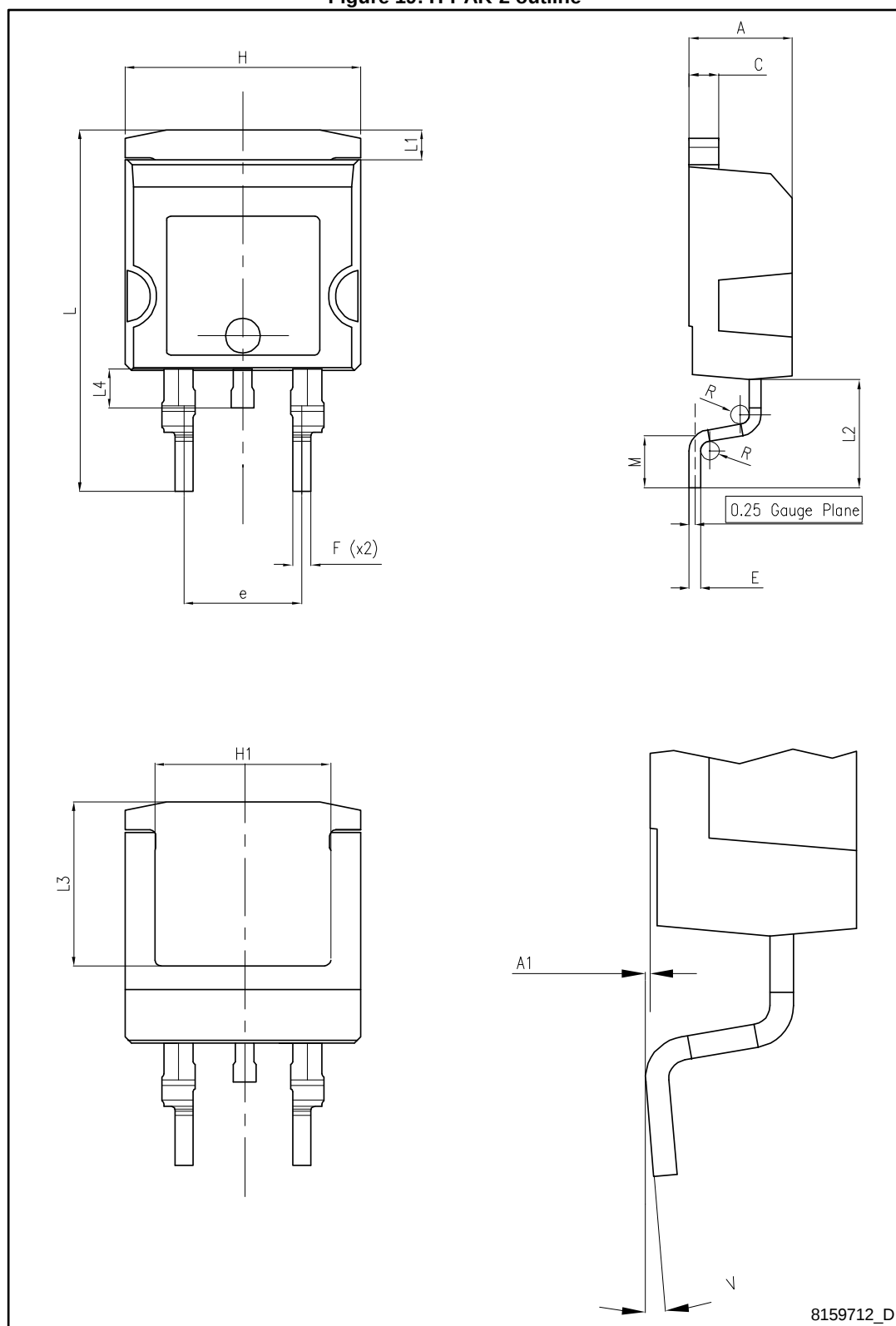
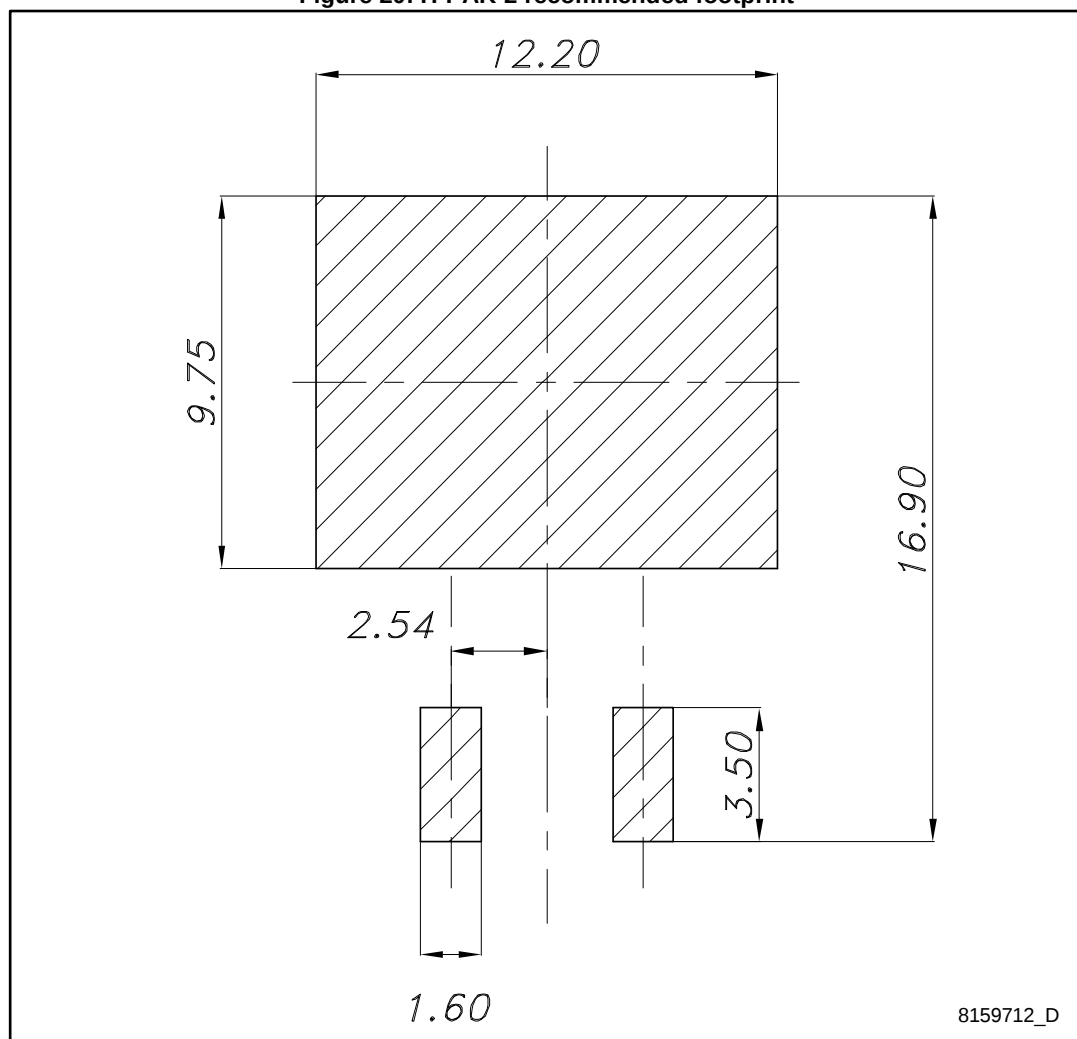
Figure 19: H²PAK-2 outline

Table 8: H²PAK-2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 20: H²PAK-2 recommended footprint

4.2 Packing information

Figure 21: Tape outline

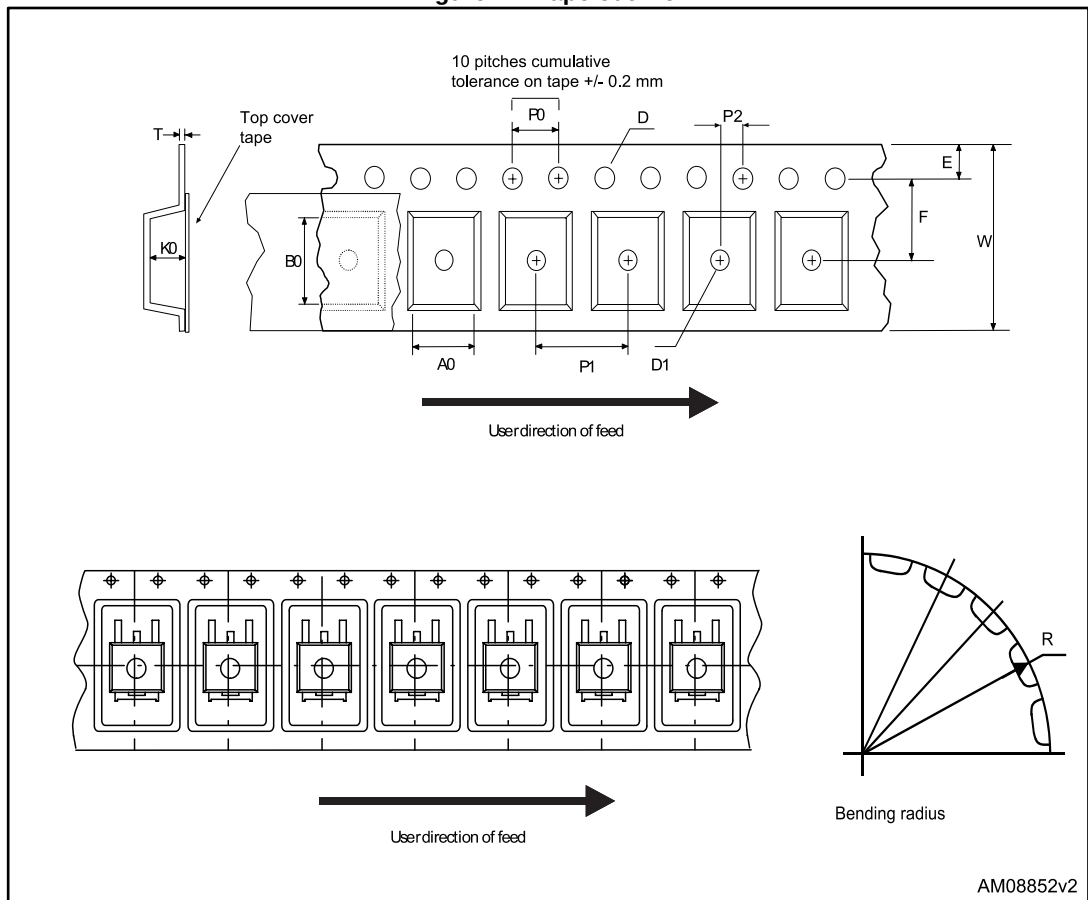


Figure 22: Reel outline

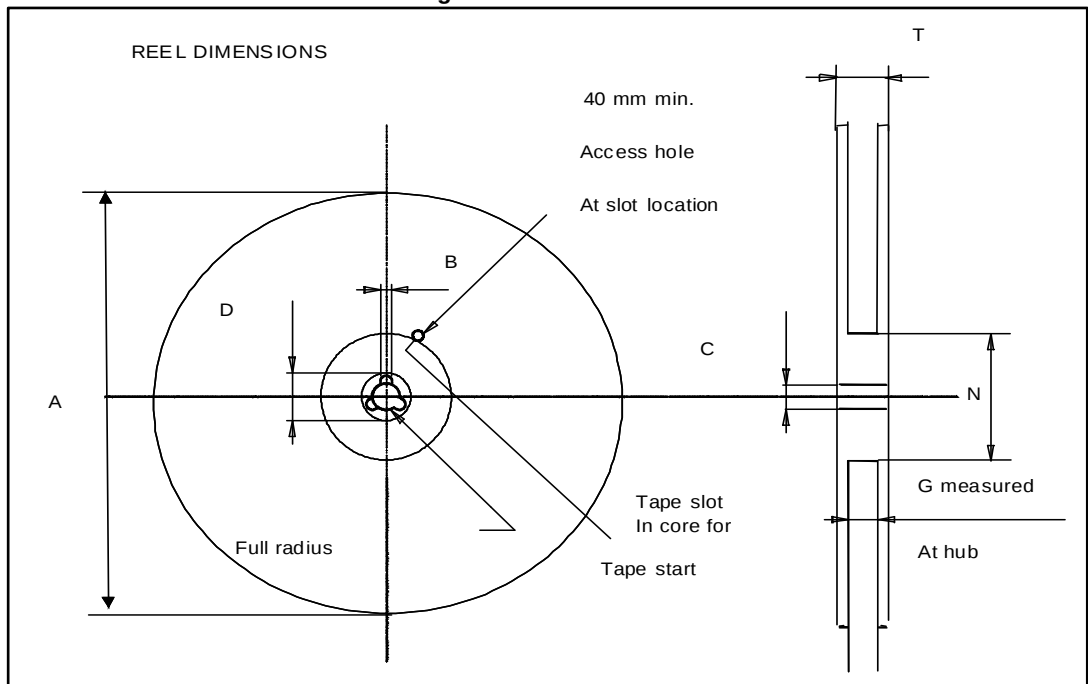


Table 9: Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
18-Jul-2011	1	First version
26-Nov-2014	2	• Modified fig 2. • Updated package mechanical data. • Updated the title, features and description.

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